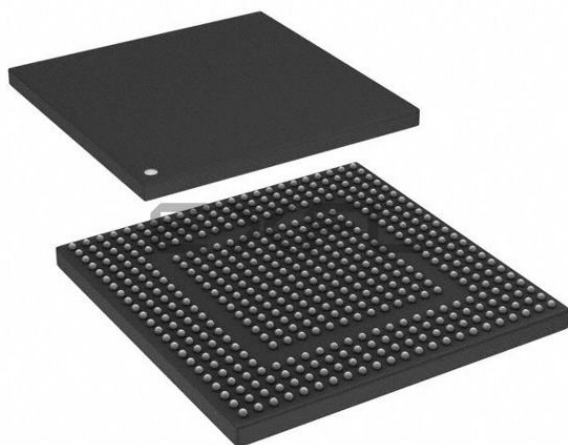




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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	ARM1136JF-S
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Multimedia; GPU, IPU, MPEG-4, VFP
RAM Controllers	DDR
Graphics Acceleration	Yes
Display & Interface Controllers	Keyboard, Keypad, LCD
Ethernet	-
SATA	-
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.0V, 2.5V, 2.7V, 3.0V
Operating Temperature	-40°C ~ 85°C (TA)
Security Features	Random Number Generator, RTIC, Secure Fusebox, Secure JTAG, Secure Memory
Package / Case	473-LFBGA
Supplier Device Package	473-LFBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx31cvmn4dr2

Table 7 provides the operating ranges.

NOTE

The term NVCC in this section refers to the associated supply rail of an input or output. The association is shown in the Signal Multiplexing chapter of the reference manual.

CAUTION

NVCC6 and NVCC9 must be at the same voltage potential. These supplies are connected together on-chip to optimize ESD damage immunity.

Table 7. Operating Ranges

Symbol	Parameter	Min	Max	Units
QVCC, QVCC1, QVCC4	Core Operating Voltage ^{1,2} $0 \leq f_{\text{ARM}} \leq 400 \text{ MHz}$	1.22	1.47	V
	State Retention Voltage ³	0.95	—	
NVCC1, NVCC3–10	I/O Supply Voltage, except DDR ⁴	1.75	3.1	V
NVCC2, NVCC21, NVCC22	I/O Supply Voltage, DDR only	1.75	1.95	V
FVCC, MVCC, SVCC, UVCC	PLL (Phase-Locked Loop) and FPM (Frequency Pre-multiplier) Supply Voltage ⁵	1.3	1.47	V
IOQVDD	On-device Level Shifter Supply Voltage	1.6	1.9	V
FUSE_VDD	Fusebox read Supply Voltage ⁶	—	—	V
	Fusebox write (program) Supply Voltage ⁷	3.0	3.3	V
T _A	Operating Ambient Temperature Range	–40	85	°C
T _j	Operating Junction Temperature Range	—	105	°C

¹ Measured at package balls, including peripherals, ARM, and L2 cache supplies (QVCC, QVCC1, QVCC4, respectively).

² The core voltage must be higher than 1.38V to avoid corrupted data during transfers from the USB HS. Please refer to Errata file ENGcm02610 ID

³ The SR voltage is applied to QVCC, QVCC1, and QVCC4 after the device is placed in SR mode. The Real-Time Clock (RTC) is operational in State Retention (SR) mode.

⁴ Overshoot and undershoot conditions (transitions above NVCC and below GND) on I/O must be held below 0.6 V, and the duration of the overshoot/undershoot must not exceed 10% of the system clock cycle. Overshoot/undershoot must be controlled through printed circuit board layout, transmission line impedance matching, signal line termination, or other methods. Non-compliance to this specification may affect device reliability or cause permanent damage to the device.

⁵ PLL voltage must not be altered after power-up, otherwise the PLL will be unstable and lose lock. To minimize inducing noise on the PLL supply line, source the voltage from a low-noise, dedicated supply. PLL parameters in [Table 28, "DPLL Specifications," on page 31](#), are guaranteed over the entire specified voltage range.

⁶ In read mode, FUSE_VDD can be floated or grounded.

⁷ Fuses might be inadvertently blown if written to while the voltage is below this minimum.

Table 8. Specific Operating Ranges for Silicon Revision 2.0 and 2.0.1

Symbol	Parameter	Min	Max	Units
FUSE_VDD	Fusebox read Supply Voltage ¹	—	—	V
	Fusebox write (program) Supply Voltage ²	3.0	3.3	V

4.2 Supply Power-Up/Power-Down Requirements and Restrictions

Any MCIMX31C board design must comply with the power-up and power-down sequence guidelines as described in this section to guarantee reliable operation of the device. Any deviation from these sequences may result in any or all of the following situations:

- Cause excessive current during power-up phase
- Prevent the device from booting
- Cause irreversible damage to the MCIMX31C (worst-case scenario)

4.2.1 Powering Up

The Power On Reset ($\overline{\text{POR}}$) pin must be kept asserted (low) throughout the power-up sequence. Power-up logic must guarantee that all power sources reach their target values prior to the release (de-assertion) of $\overline{\text{POR}}$. Figure 2 and Figure 3 show two options of the power-up sequence.

NOTE

Stages need to be performed in the order shown; however, *within* each stage, supplies can be powered up in any order. For example, supplies IOQVDD, NVCC1, and NVCC3 through NVCC10 do not need to be powered up in the order shown.

CAUTION

NVCC6 and NVCC9 must be at the same voltage potential. These supplies are connected together on-chip to optimize ESD damage immunity.

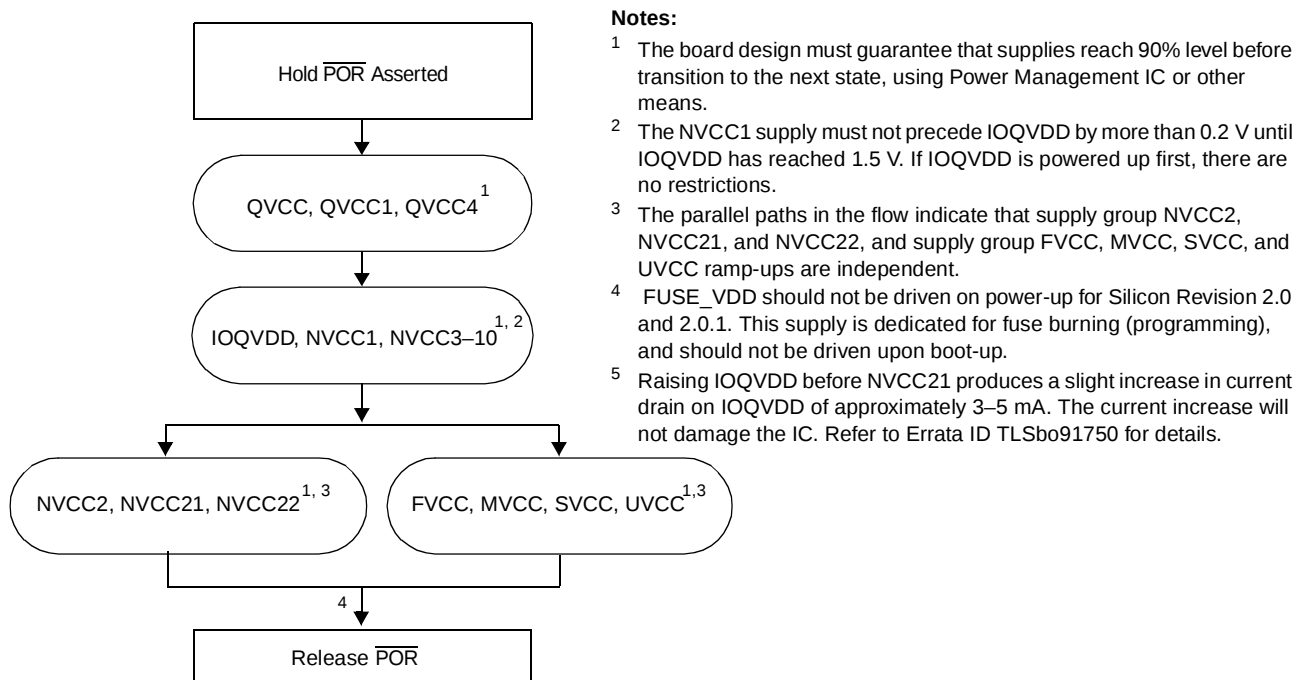


Figure 2. Option 1 Power-Up Sequence for Silicon Revision 2.0 and 2.0.1

Electrical Characteristics

When bus buffers are used, the ata_data bus buffer is special. This is a bidirectional bus buffer, so a direction control signal is needed. This direction control signal is ata_buffer_en. When its high, the bus should drive from host to device. When its low, the bus should drive from device to host. Steering of the signal is such that contention on the host and device tri-state busses is always avoided.

4.3.5.1 Timing Parameters

In the timing equations, some timing parameters are used. These parameters depend on the implementation of the ATA interface on silicon, the bus buffer used, the cable delay and cable skew. [Table 21](#) shows ATA timing parameters.

Table 21. ATA Timing Parameters

Name	Description	Value/ Contributing Factor ¹
T	Bus clock period (ipg_clk_ata)	peripheral clock frequency
ti_ds	Set-up time ata_data to ata_iordy edge (UDMA-in only) UDMA0 UDMA1 UDMA2, UDMA3 UDMA4 UDMA5	15 ns 10 ns 7 ns 5 ns 4 ns
ti_dh	Hold time ata_iordy edge to ata_data (UDMA-in only) UDMA0, UDMA1, UDMA2, UDMA3, UDMA4 UDMA5	5.0 ns 4.6 ns
tco	Propagation delay bus clock L-to-H to ata_cs0, ata_cs1, ata_da2, ata_da1, ata_da0, ata_dior, ata_diow, ata_dmack, ata_data, ata_buffer_en	12.0 ns
tsu	Set-up time ata_data to bus clock L-to-H	8.5 ns
tsui	Set-up time ata_iordy to bus clock H-to-L	8.5 ns
thi	Hold time ata_iordy to bus clock H to L	2.5 ns
tskew1	Max difference in propagation delay bus clock L-to-H to any of following signals ata_cs0, ata_cs1, ata_da2, ata_da1, ata_da0, ata_dior, ata_diow, ata_dmack, ata_data (write), ata_buffer_en	7 ns
tskew2	Max difference in buffer propagation delay for any of following signals ata_cs0, ata_cs1, ata_da2, ata_da1, ata_da0, ata_dior, ata_diow, ata_dmack, ata_data (write), ata_buffer_en	transceiver
tskew3	Max difference in buffer propagation delay for any of following signals ata_iordy, ata_data (read)	transceiver
tbuf	Max buffer propagation delay	transceiver
tcable1	Cable propagation delay for ata_data	cable
tcable2	Cable propagation delay for control signals ata_dior, ata_diow, ata_iordy, ata_dmack	cable
tskew4	Max difference in cable propagation delay between ata_iordy and ata_data (read)	cable

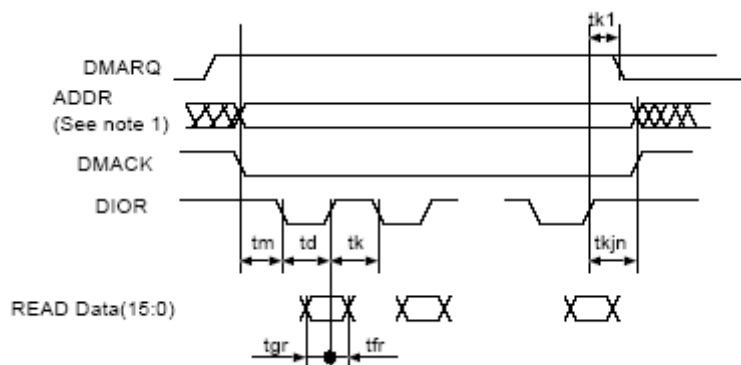


Figure 12. MDMA Read Timing Diagram

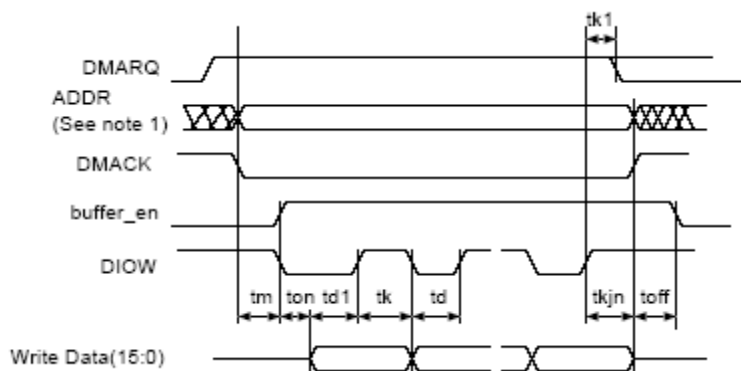


Figure 13. MDMA Write Timing Diagram

Table 24. MDMA Read and Write Timing Parameters

ATA Parameter	Parameter from Figure 12, Figure 13	Value	Controlling Variable
tm, ti	tm	$tm(\min) = ti(\min) = time_m * T - (tskew1 + tskew2 + tskew5)$	time_m
td	td, td1	$td1(\min) = td(\min) = time_d * T - (tskew1 + tskew2 + tskew6)$	time_d
tk	tk	$tk(\min) = time_k * T - (tskew1 + tskew2 + tskew6)$	time_k
t0	—	$t0(\min) = (time_d + time_k) * T$	time_d, time_k
tg(read)	tgr	$tgr(\min-read) = tco + tsu + tbuf + tbuf + tcable1 + tcable2$ $tgr(\min-drive) = td - te(drive)$	time_d
tf(read)	tfr	$tfr(\min-drive) = 0$	—
tg(write)	—	$tg(\min-write) = time_d * T - (tskew1 + tskew2 + tskew5)$	time_d
tf(write)	—	$tf(\min-write) = time_k * T - (tskew1 + tskew2 + tskew6)$	time_k
tL	—	$tL(\max) = (time_d + time_k - 2) * T - (tsu + tco + 2 * tbuf + 2 * tcable2)$	time_d, time_k
tn, tj	tkjn	$tn = tj = tkjn = (\max(time_k, time_jn) * T - (tskew1 + tskew2 + tskew6))$	time_jn
—	ton toff	$ton = time_on * T - tskew1$ $toff = time_off * T - tskew1$	—

4.3.5.3 UDMA In Timing

Figure 14 shows timing when the UDMA in transfer starts, Figure 15 shows timing when the UDMA in host terminates transfer, Figure 16 shows timing when the UDMA in device terminates transfer, and Table 25 lists the timing parameters for UDMA in burst.

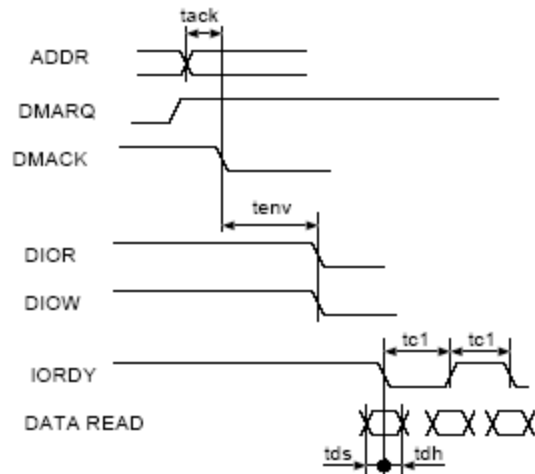


Figure 14. UDMA In Transfer Starts Timing Diagram

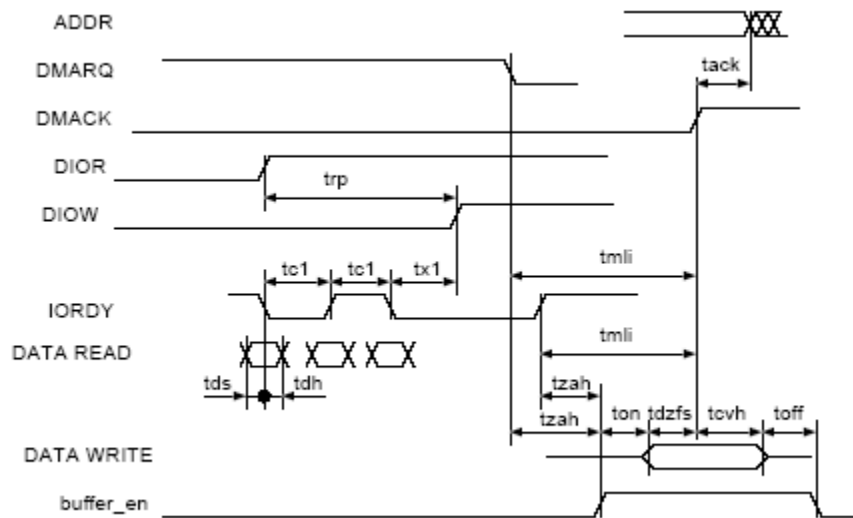


Figure 15. UDMA In Host Terminates Transfer Timing Diagram

4.3.5.4 UDMA Out Timing

Figure 17 shows timing when the UDMA out transfer starts, Figure 18 shows timing when the UDMA out host terminates transfer, Figure 19 shows timing when the UDMA out device terminates transfer, and Table 26 lists the timing parameters for UDMA out burst.

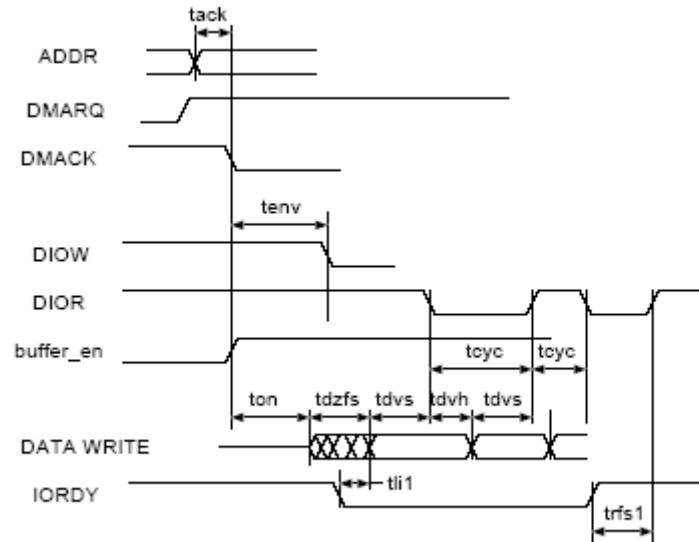


Figure 17. UDMA Out Transfer Starts Timing Diagram

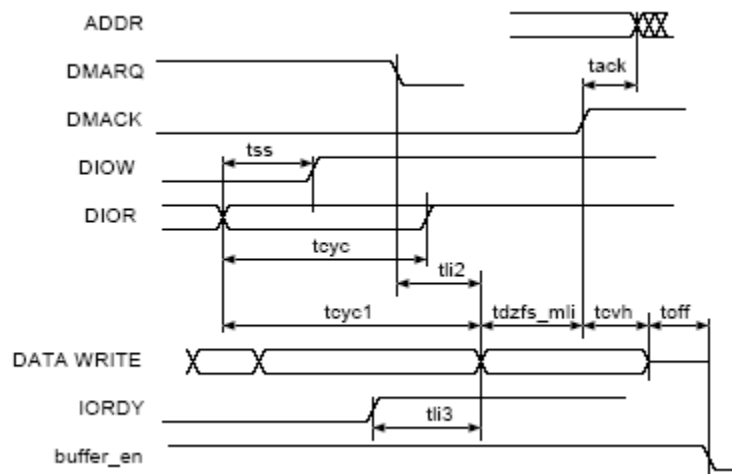


Figure 18. UDMA Out Host Terminates Transfer Timing Diagram

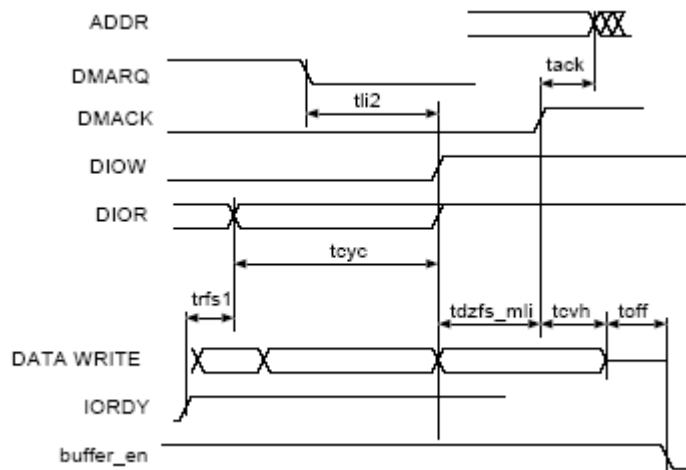


Figure 19. UDMA Out Device Terminates Transfer Timing Diagram

Table 26. UDMA Out Burst Timing Parameters

ATA Parameter	Parameter from Figure 17, Figure 18, Figure 19	Value	Controlling Variable
tack	tack	$tack (min) = (time_ack * T) - (tskew1 + tskew2)$	time_ack
tenv	tenv	$tenv (min) = (time_env * T) - (tskew1 + tskew2)$ $tenv (max) = (time_env * T) + (tskew1 + tskew2)$	time_env
tdvs	tdvs	$tdvs = (time_dvs * T) - (tskew1 + tskew2)$	time_dvs
tdvh	tdvh	$tdvs = (time_dvh * T) - (tskew1 + tskew2)$	time_dvh
tcyc	tcyc	$tcyc = time_cyc * T - (tskew1 + tskew2)$	time_cyc
t2cyc	—	$t2cyc = time_cyc * 2 * T$	time_cyc
trfs1	trfs	$trfs = 1.6 * T + tsui + tco + tbuf + tbuf$	—
—	tdzfs	$tdzfs = time_dzfs * T - (tskew1)$	time_dzfs
tss	tss	$tss = time_ss * T - (tskew1 + tskew2)$	time_ss
tmli	tdzfs_mli	$tdzfs_mli = \max (time_dzfs, time_mli) * T - (tskew1 + tskew2)$	—
tli	tli1	$tli1 > 0$	—
tli	tli2	$tli2 > 0$	—
tli	tli3	$tli3 > 0$	—
tcvh	tcvh	$tcvh = (time_cvh * T) - (tskew1 + tskew2)$	time_cvh
—	ton toff	$ton = time_on * T - tskew1$ $toff = time_off * T - tskew1$	—

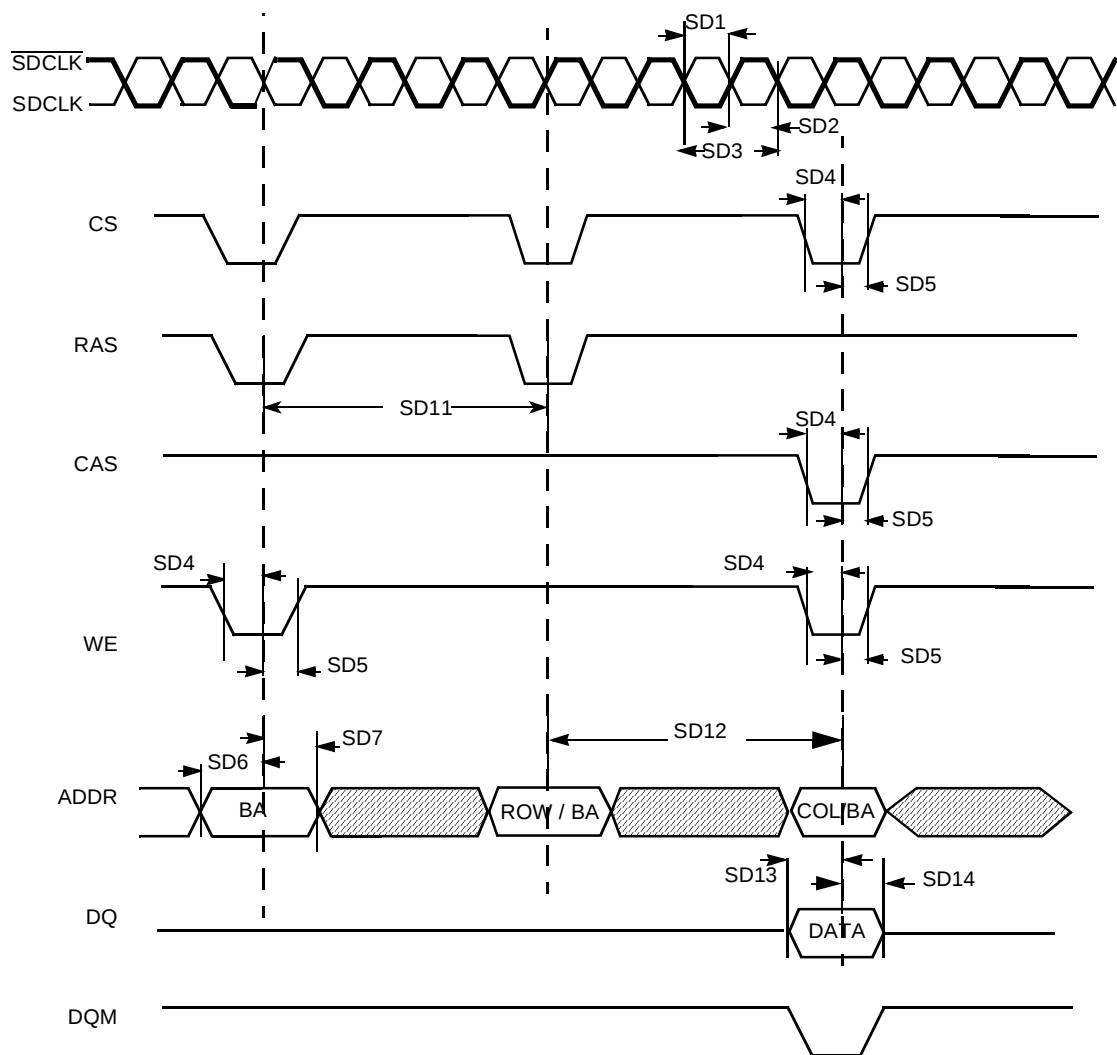


Figure 34. SDR SDRAM Write Cycle Timing Diagram

Table 32. SDR SDRAM Write Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
SD1	SDRAM clock high-level width	tCH	3.4	4.1	ns
SD2	SDRAM clock low-level width	tCL	3.4	4.1	ns
SD3	SDRAM clock cycle time	tCK	7.5	—	ns
SD4	CS, RAS, CAS, WE, DQM, CKE setup time	tCMS	2.0	—	ns
SD5	CS, RAS, CAS, WE, DQM, CKE hold time	tCMH	1.8	—	ns
SD6	Address setup time	tAS	2.0	—	ns
SD7	Address hold time	tAH	1.8	—	ns
SD11	Precharge cycle period ¹	tRP	1	4	clock
SD12	Active to read/write command delay ¹	tRCD	1	8	clock

Table 32. SDR SDRAM Write Timing Parameters (continued)

ID	Parameter	Symbol	Min	Max	Unit
SD13	Data setup time	tDS	2.0	—	ns
SD14	Data hold time	tDH	1.3	—	ns

¹ SD11 and SD12 are determined by SDRAM controller register settings.

NOTE

SDR SDRAM CLK parameters are being measured from the 50% point—that is, high is defined as 50% of signal value and low is defined as 50% of signal value.

NOTE

The timing parameters are similar to the ones used in SDRAM data sheets—that is, [Table 32](#) indicates SDRAM requirements. All output signals are driven by the ESDCTL at the negative edge of SDCLK and the parameters are measured at maximum memory frequency.

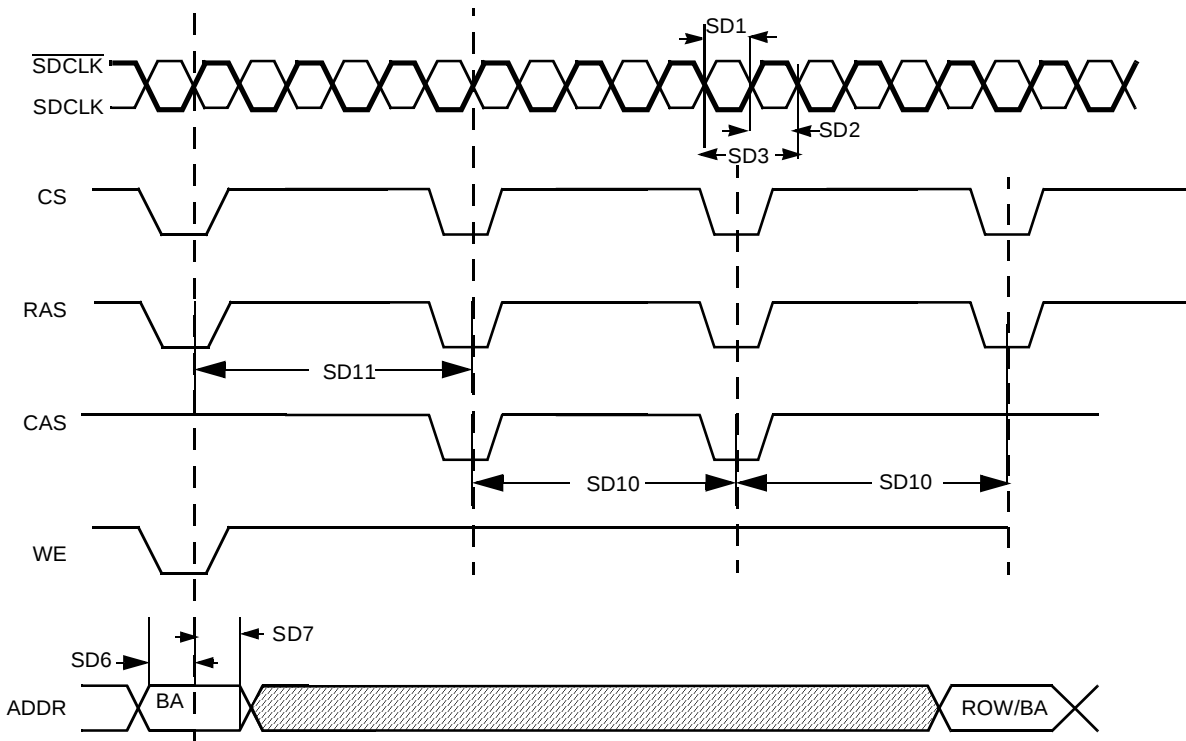
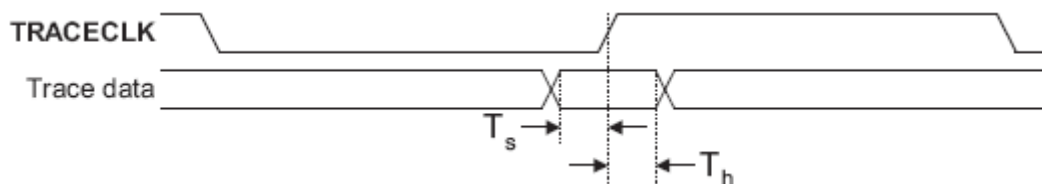


Figure 35. SDRAM Refresh Timing Diagram

Table 37. ETM TRACECLK Timing Parameters

ID	Parameter	Min	Max	Unit
T_{cyc}	Clock period	Frequency dependent	—	ns
T_{wl}	Low pulse width	2	—	ns
T_{wh}	High pulse width	2	—	ns
T_r	Clock and data rise time	—	3	ns
T_f	Clock and data fall time	—	3	ns

Figure 40 depicts the setup and hold requirements of the trace data pins with respect to TRACECLK, and Table 38 lists the timing parameters.


Figure 40. Trace Data Timing Diagram
Table 38. ETM Trace Data Timing Parameters

ID	Parameter	Min	Max	Unit
T_s	Data setup	2	—	ns
T_h	Data hold	1	—	ns

4.3.10.1 Half-Rate Clocking Mode

When half-rate clocking is used, the trace data signals are sampled by the TPA on both the rising and falling edges of TRACECLK, where TRACECLK is half the frequency of the clock shown in Figure 40.

4.3.11 FIR Electrical Specifications

FIR implements asynchronous infrared protocols (FIR, MIR) that are defined by IrDA[®] (Infrared Data Association). Refer to <http://www.IrDA.org> for details on FIR and MIR protocols.

4.3.12 Fusebox Electrical Specifications

Table 39. Fusebox Timing Characteristics

Ref. Num	Description	Symbol	Minimum	Typical	Maximum	Units
1	Program time for eFuse ¹	$t_{program}$	125	—	—	μs

¹ The program length is defined by the value defined in the epm_pgm_length[2:0] bits of the IIM module. The value to program is based on a 32 kHz clock source ($4 * 1/32 \text{ kHz} = 125 \mu s$)

4.3.13 I²C Electrical Specifications

This section describes the electrical information of the I²C Module.

4.3.13.1 I²C Module Timing

Figure 41 depicts the timing of I²C module. Table 40 lists the I²C module timing parameters where the I/O supply is 2.7 V. 1

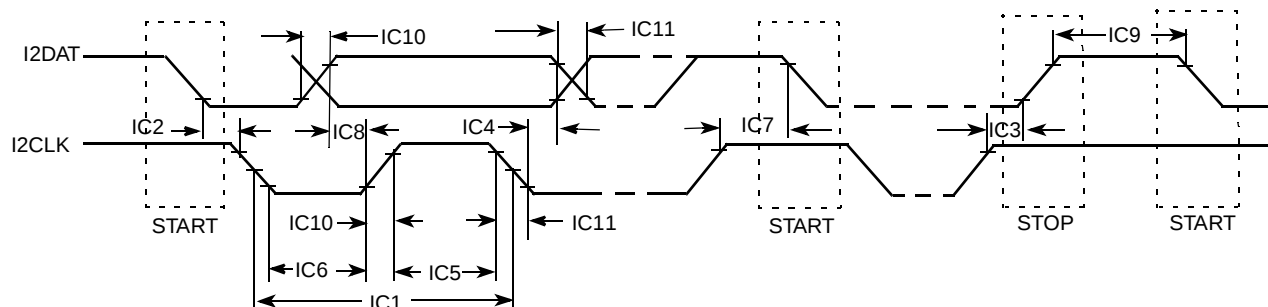


Figure 41. I²C Bus Timing Diagram

Table 40. I²C Module Timing Parameters—I²C Pin I/O Supply=2.7 V

ID	Parameter	Standard Mode		Fast Mode		Unit
		Min	Max	Min	Max	
IC1	I2CLK cycle time	10	—	2.5	—	μs
IC2	Hold time (repeated) START condition	4.0	—	0.6	—	μs
IC3	Set-up time for STOP condition	4.0	—	0.6	—	μs
IC4	Data hold time	0 ¹	3.45 ²	0 ¹	0.9 ²	μs
IC5	HIGH Period of I2CLK Clock	4.0	—	0.6	—	μs
IC6	LOW Period of the I2CLK Clock	4.7	—	1.3	—	μs
IC7	Set-up time for a repeated START condition	4.7	—	0.6	—	μs
IC8	Data set-up time	250	—	100 ³	—	ns
IC9	Bus free time between a STOP and START condition	4.7	—	1.3	—	μs
IC10	Rise time of both I2DAT and I2CLK signals	—	1000	20+0.1C _b ⁴	300	ns
IC11	Fall time of both I2DAT and I2CLK signals	—	300	20+0.1C _b ⁴	300	ns
IC12	Capacitive load for each bus line (C _b)	—	400	—	400	pF

¹ A device must internally provide a hold time of at least 300 ns for I2DAT signal in order to bridge the undefined region of the falling edge of I2CLK.

² The maximum hold time has to be met only if the device does not stretch the LOW period (ID IC6) of the I2CLK signal.

³ A Fast-mode I²C-bus device can be used in a standard-mode I²C-bus system, but the requirement of set-up time (ID IC7) of 250 ns must then be met. This will automatically be the case if the device does not stretch the LOW period of the I2CLK signal. If such a device does stretch the LOW period of the I2CLK signal, it must output the next data bit to the I2DAT line max_rise_time (ID No IC10) + data_setup_time (ID No IC8) = 1000 + 250 = 1250 ns (according to the Standard-mode I²C-bus specification) before the I2CLK line is released.

⁴ C_b = total capacitance of one bus line in pF.

Electrical Characteristics

³ Display interface clock up time

$$T_{dicu} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot \text{DISP3_IF_CLK_UP_WR}}{HSP_CLK_PERIOD} \right]$$

where CEIL(X) rounds the elements of X to the nearest integers towards infinity.

4.3.15.3 Interface to Sharp HR-TFT Panels

Figure 49 depicts the Sharp HR-TFT panel interface timing, and Table 46 lists the timing parameters. The CLS_RISE_DELAY, CLS_FALL_DELAY, PS_FALL_DELAY, PS_RISE_DELAY, REV_TOGGLE_DELAY parameters are defined in the SDC_SHARP_CONF_1 and SDC_SHARP_CONF_2 registers. For other Sharp interface timing characteristics, refer to Section 4.3.15.2.2, “Interface to Active Matrix TFT LCD Panels, Electrical Characteristics,” on page 55. The timing images correspond to straight polarity of the Sharp signals.

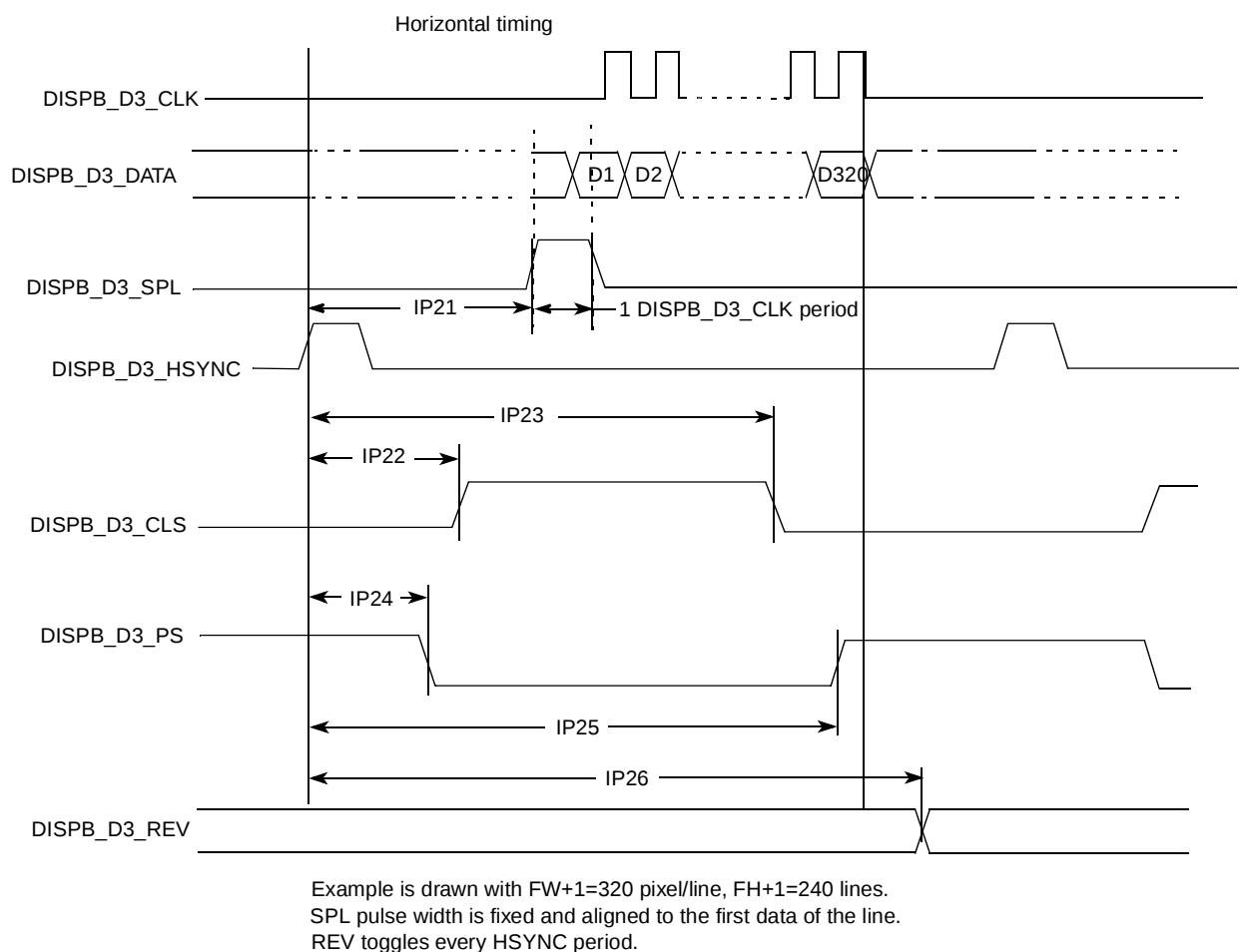


Figure 49. Sharp HR-TFT Panel Interface Timing Diagram—Pixel Level

Electrical Characteristics

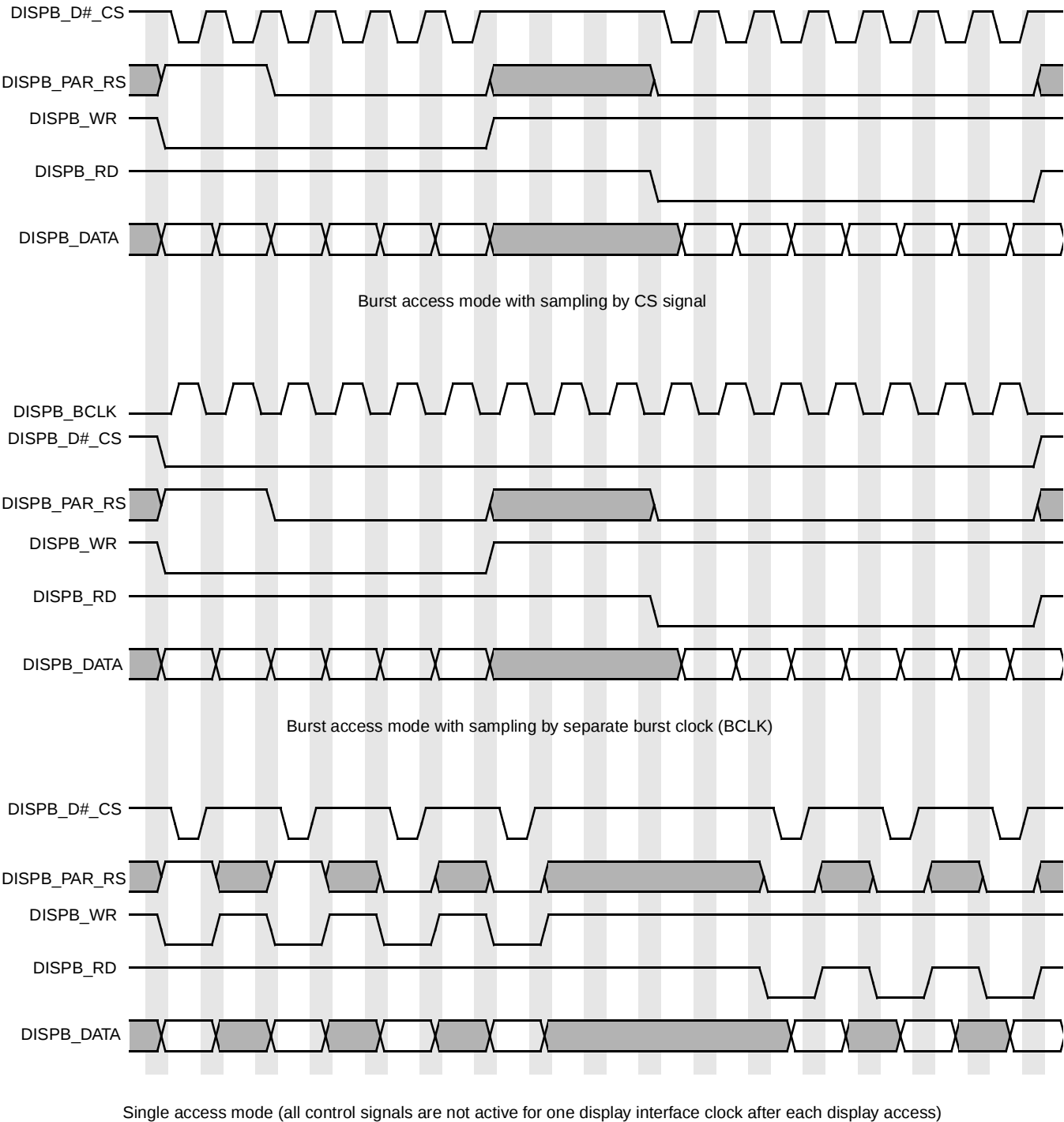


Figure 51. Asynchronous Parallel System 80 Interface (Type 1) Burst Mode Timing Diagram

Table 47. Asynchronous Parallel Interface Timing Parameters—Access Level (continued)

ID	Parameter	Symbol	Min.	Typ. ¹	Max.	Units
IP36	Controls hold time for write	Tdchw	Tdicpw–Tdicdw–1.5	Tdicpw–Tdicdw	—	ns
IP37	Slave device data delay ⁸	Tracc	0	—	Tdrp ⁹ –Tlbd ¹⁰ –Tdicur–1.5	ns
IP38	Slave device data hold time ⁸	Troh	Tdrp–Tlbd–Tdicdr+1.5	—	Tdicpr–Tdicdr–1.5	ns
IP39	Write data setup time	Tds	Tdicdw–1.5	Tdicdw	—	ns
IP40	Write data hold time	Tdh	Tdicpw–Tdicdw–1.5	Tdicpw–Tdicdw	—	ns
IP41	Read period ²	Tdicpr	Tdicpr–1.5	Tdicpr	Tdicpr+1.5	ns
IP42	Write period ³	Tdicpw	Tdicpw–1.5	Tdicpw	Tdicpw+1.5	ns
IP43	Read down time ⁴	Tdicdr	Tdicdr–1.5	Tdicdr	Tdicdr+1.5	ns
IP44	Read up time ⁵	Tdicur	Tdicur–1.5	Tdicur	Tdicur+1.5	ns
IP45	Write down time ⁶	Tdicdw	Tdicdw–1.5	Tdicdw	Tdicdw+1.5	ns
IP46	Write up time ⁷	Tdicuw	Tdicuw–1.5	Tdicuw	Tdicuw+1.5	ns
IP47	Read time point ⁹	Tdrp	Tdrp–1.5	Tdrp	Tdrp+1.5	ns

¹The exact conditions have not been finalized, but will likely match the current customer requirement for their specific display. These conditions may be device specific.

² Display interface clock period value for read:

$$T_{dicpr} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP\#_IF_CLK_PER_RD}{HSP_CLK_PERIOD} \right]$$

³ Display interface clock period value for write:

$$T_{dicpw} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP\#_IF_CLK_PER_WR}{HSP_CLK_PERIOD} \right]$$

⁴ Display interface clock down time for read:

$$T_{dicdr} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_DOWN_RD}{HSP_CLK_PERIOD} \right]$$

⁵ Display interface clock up time for read:

$$T_{dicur} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_UP_RD}{HSP_CLK_PERIOD} \right]$$

⁶ Display interface clock down time for write:

$$T_{dicdw} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_DOWN_WR}{HSP_CLK_PERIOD} \right]$$

⁷ Display interface clock up time for write:

$$T_{dicuw} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_UP_WR}{HSP_CLK_PERIOD} \right]$$

⁸ This parameter is a requirement to the display connected to the IPU

⁹ Data read point

$$T_{drp} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP\#_READ_EN}{HSP_CLK_PERIOD} \right]$$

¹⁰ Loopback delay Tlbd is the cumulative propagation delay of read controls and read data. It includes an IPU output delay, a device-level output delay, board delays, a device-level input delay, an IPU input delay. This value is device specific.

The DISP#_IF_CLK_PER_WR, DISP#_IF_CLK_PER_RD, HSP_CLK_PERIOD, DISP#_IF_CLK_DOWN_WR, DISP#_IF_CLK_UP_WR, DISP#_IF_CLK_DOWN_RD, DISP#_IF_CLK_UP_RD and DISP#_READ_EN parameters are programmed via the DI_DISP#_TIME_CONF_1, DI_DISP#_TIME_CONF_2 and DI_HSP_CLK_PER Registers.

4.3.15.5.3 Serial Interfaces, Functional Description

The IPU supports the following types of asynchronous serial interfaces:

- 3-wire (with bidirectional data line)
- 4-wire (with separate data input and output lines)
- 5-wire type 1 (with sampling RS by the serial clock)
- 5-wire type 2 (with sampling RS by the chip select signal)

Figure 60 depicts timing of the 3-wire serial interface. The timing images correspond to active-low DISPB_D#_CS signal and the straight polarity of the DISPB_SD_D_CLK signal.

For this interface, a bidirectional data line is used outside the device. The IPU still uses separate input and output data lines (IPP_IND_DISP_B_SD_D and IPP_DO_DISP_B_SD_D). The I/O mux should provide joining the internal data lines to the bidirectional external line according to the IPP_OBE_DISP_B_SD_D signal provided by the IPU.

Each data transfer can be preceded by an optional preamble with programmable length and contents. The preamble is followed by read/write (RW) and address (RS) bits. The order of the these bits is programmable. The RW bit can be disabled. The following data can consist of one word or of a whole burst. The interface parameters are controlled by the DI_SER_DISP1_CONF and DI_SER_DISP2_CONF Registers.

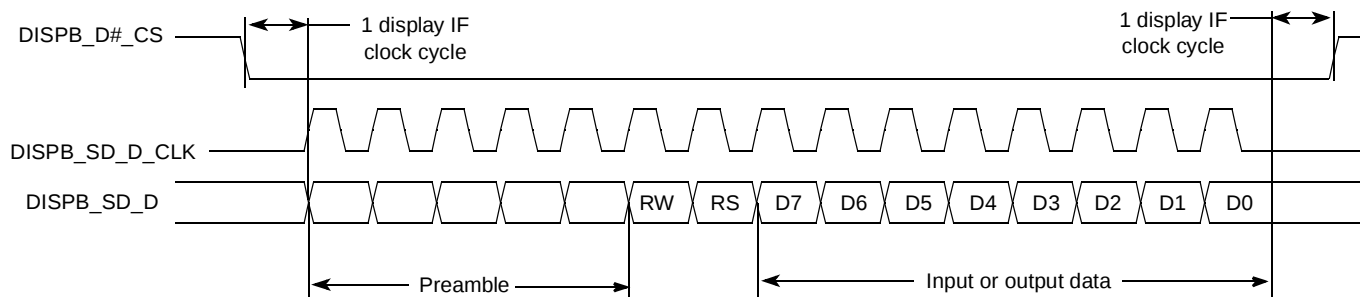


Figure 60. 3-Wire Serial Interface Timing Diagram

Figure 61 depicts timing of the 4-wire serial interface. For this interface, there are separate input and output data lines both inside and outside the device.

Table 50. Parallel Interface Timing Parameters¹

Signal	Parameter	Symbol	Standards		Unit
			Min	Max	
MSHC_SCLK	Cycle	tSCLKc	25	—	ns
	H pulse length	tSCLKwh	5	—	ns
	L pulse length	tSCLKwl	5	—	ns
	Rise time	tSCLKr	—	10	ns
	Fall time	tSCLKf	—	10	ns
MSHC_BS	Setup time	tBSSu	8	—	ns
	Hold time	tBSh	1	—	ns
MSHC_DATA	Setup time	tDsu	8	—	ns
	Hold time	tDh	1	—	ns
	Output delay time	tDd	—	15	ns

¹ Timing is guaranteed for NVCC from 2.7 through 3.1 V. See NVCC restrictions described in [Table 7, "Operating Ranges,"](#) on [page 12](#).

4.3.17 Personal Computer Memory Card International Association (PCMCIA)

[Figure 68](#) and [Figure 69](#) depict the timings pertaining to the PCMCIA module, each of which is an example of one clock of strobe set-up time and one clock of strobe hold time. [Table 51](#) lists the timing parameters.

The interface is meant to be used with synchronous SIM cards. This means that the SIM module provides a clock for the SIM card to use. The frequency of this clock is normally 372 times the data rate on the TX/RX pins, however SIM module can work with CLK equal to 16 times the data rate on TX/RX pins.

There is no timing relationship between the clock and the data. The clock that the SIM module provides to the aim card will be used by the SIM card to recover the clock from the data much like a standard UART. All six (or 5 in case bi directional TXRX is used) of the pins for each half of the SIM module are asynchronous to each other.

There are no required timing relationships between the signals in normal mode, but there are some in two specific cases: reset and power down sequences.

4.3.20.1 General Timing Requirements

Figure 72 shows the timing of the SIM module, and Figure 54 lists the timing parameters.

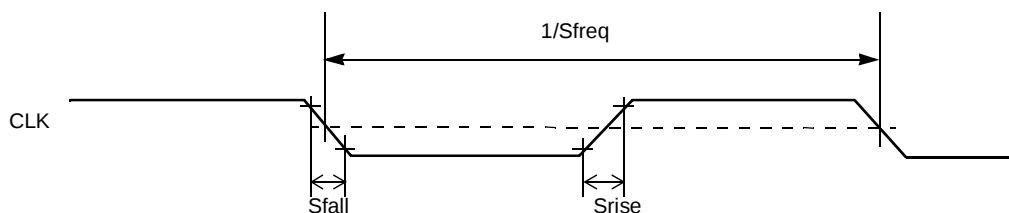


Figure 72. SIM Clock Timing Diagram

Table 54. SIM Timing Specification—High Drive Strength

Num	Description	Symbol	Min	Max	Unit
1	SIM Clock Frequency (CLK) ¹	S_{freq}	0.01	5 (Some new cards may reach 10)	MHz
2	SIM CLK Rise Time ²	S_{rise}	—	20	ns
3	SIM CLK Fall Time ³	S_{fall}	—	20	ns
4	SIM Input Transition Time (RX, SIMPD)	S_{trans}	—	25	ns

¹ 50% duty cycle clock

² With C = 50pF

³ With C = 50pF

4.3.20.2 Reset Sequence

4.3.20.2.1 Cards with Internal Reset

The sequence of reset for this kind of SIM Cards is as follows (see Figure 73):

- After powerup, the clock signal is enabled on SGCLK (time T0)
- After 200 clock cycles, RX must be high.
- The card must send a response on RX acknowledging the reset between 400 and 40000 clock cycles after T0.

Table 63. 19 x 19 BGA No Connects¹

Signal	Ball Location
NC	N7
NC	P7
NC	U21

¹ These contacts are not used and must be floated by the user.

5.1.3.2 BGA Signal ID by Ball Grid Location—19 x 19 0.8 mm

Table 64. 19 x 19 BGA Signal ID by Ball Grid Location

Signal ID	Ball Location	Signal ID	Ball Location
A0	Y6	CKIL	E21
A1	AC5	CLKO	C20
A10	V15	CLKSS	H17
A11	AB3	COMPARE	A20
A12	AA3	CONTRAST	N21
A13	Y3	CS0	U17
A14	Y15	CS1	Y22
A15	Y14	CS2	Y18
A16	V14	CS3	Y19
A17	Y13	CS4	Y20
A18	V13	CS5	AA21
A19	Y12	CSI_D10	K21
A2	AB5	CSI_D11	K22
A20	V12	CSI_D12	K23
A21	Y11	CSI_D13	L20
A22	V11	CSI_D14	L18
A23	Y10	CSI_D15	L21
A24	Y9	CSI_D4	J20
A25	Y8	CSI_D5	J21
A3	AA5	CSI_D6	L17
A4	Y5	CSI_D7	J22
A5	AC4	CSI_D8	J23
A6	AB4	CSI_D9	K20
A7	AA4	CSI_HSYNC	H22
A8	Y4	CSI_MCLK	H20
A9	AC3	CSI_PIXCLK	H23
ATA_CS0	E1	CSI_VSYNC	H21
ATA_CS1	G4	CSPI1_MISO	N2
ATA_DIOR	E3	CSPI1_MOSI	N1
ATA_DIOW	H6	CSPI1_SCLK	M4
ATA_DMACK	E2	CSPI1_SPI_RDY	M1
ATA_RESET	F3	CSPI1_SS0	M2
BATT_LINE	F6	CSPI1_SS1	N6
BCLK	W20	CSPI1_SS2	M3
BOOT_MODE0	F17	CSPI2_MISO	B4
BOOT_MODE1	C21	CSPI2_MOSI	D5

Table 64. 19 x 19 BGA Signal ID by Ball Grid Location (continued)

Signal ID	Ball Location	Signal ID	Ball Location
EB1	W21	LD17	W23
ECB	Y21	LD2	R21
FPSHIFT	M23	LD3	R20
GPIO1_0	C19	LD4	T23
GPIO1_1	G17	LD5	T22
GPIO1_2	B20	LD6	T21
LD7	T20	SCK6	R2
LD8	R17	SCLK0	B19
LD9	U23	SD_D_CLK	M21
M_GRANT	U18	SD_D_I	M20
M_REQUEST	T17	SD_D_IO	M18
MA10	Y2	SD0	AC18
MCUPG	See VPG0	SD1	AA17
NFALE	T2	SD1_CLK	K2
NFCE	R4	SD1_CMD	K3
NFCLE	T1	SD1_DATA0	K4
NFRB	R3	SD1_DATA1	J1
NFRE	T4	SD1_DATA2	J2
NFWE	T3	SD1_DATA3	L6
NFWP	P6	SD10	AB14
OE	T18	SD11	AC14
PAR_RS	P22	SD12	AA13
PC_BVD1	G2	SD13	AB13
PC_BVD2	H4	SD14	AC13
PC_CD1	J3	SD15	AA12
PC_CD2	H1	SD16	AC12
PC_POE	J6	SD17	AA11
PC_PWRON	K6	SD18	AB11
PC_READY	H2	SD19	AC11
PC_RST	F1	SD2	AB17
PC_RW	G3	SD20	AA10
PC_VS1	H3	SD21	AB10
PC_VS2	G1	SD22	AC10
PC_WAIT	J4	SD23	AC9
POR	F21	SD24	AA9
POWER_FAIL	F20	SD25	AC8
PWMO	F2	SD26	AB8
RAS	AA19	SD27	AC7
READ	N18	SD28	AA8
RESET_IN	F22	SD29	AB7
RI_DCE1	D10	SD3	AC17
RI_DTE1	B11	SD30	AA7
RTCK	D15	SD31	AC6
RTS1	B9	SD4	AA16
RTS2	B12	SD5	AC16
RW	V18	SD6	AA15

- *MCIMX31 Chip Errata* (order number MCIMX31CE)

The Freescale manuals are available on the Freescale Semiconductors Web site at <http://www.freescale.com/imx>. These documents may be downloaded directly from the Freescale Web site, or printed versions may be ordered. ARM Ltd. documentation is available from <http://www.arm.com>.

7 Revision History

Table 65 summarizes revisions to the *MCIMX31C/MCIMX31LC Data Sheet* since the release of Rev. 3.

Table 65. Revision History of the MCIMX31C/MCIMX31LC Data Sheet

Rev	Location	Change
4	Table 7, "Operating Ranges," on page 12	Operating Junction Temperature Range Max: changed from 100 to 105.
4.1	Table 1, "MCIMX31C and MCIMX31LC Ordering Information," on page 3	Added new part numbers MCIMX31CVMN4D and MCIMX31LCVMN4D.
4.1	Section 1.2.1, "Feature Differences Between TO2.0 and TO 2.0.1"	Added new section describing differences between silicon revisions.
4.2	Table 1, "MCIMX31C and MCIMX31LC Ordering Information," on page 3	Added new part numbers MCIMX31CJMN4C and MCIMX31LCJMN4D and a footnote.
4.3	Table 1, "MCIMX31C and MCIMX31LC Ordering Information," on page 3	Added new part number MCIMX31CJMN4D.